

IN THE SPECIFICATION:

Please amend paragraph [0013] on page 17 with the following rewritten paragraph:

--[0013] The storage capacitor 20 consists of a pre-stage gate line 2, a storage electrode 22 overlapping with the gate line with having the gate insulating film 44, the active layer 14 and the ohmic contact layer 48 therebetween, and a pixel electrode [[22]] 18 overlapping with the storage electrode 22 with having the protective film 50 therebetween and connected via a second contact hole 24 provided in the protective film 50. The storage capacitor 20 allows a pixel signal charged in the pixel electrode 18 to be maintained stably until the next pixel signal is charged.--

Please replace paragraph [0019] on page 20 with the following rewritten paragraph:

--[0019] Referring to Fig. 3B, the gate insulating film 44 is coated onto the lower substrate 42 provided with the gate metal patterns. Further, semiconductor patterns including the active layer [[13]] 14 and the ohmic contact layer 48 and source/drain metal patterns including the data line 4, the source electrode 10, the drain electrode 12, the data pad lower electrode 36 and the storage electrode 22 are sequentially formed on the gate insulating film 44 using the second mask process.--